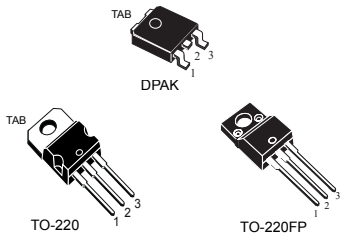
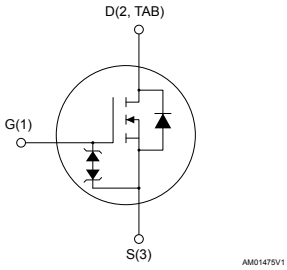
STD7NK40ZT4, STP7NK40Z, STP7NK40ZFP

Datasheet

N-channel 400 V, 0.85 Ω typ., 5.4 A, SuperMESH™ Power MOSFETs in DPAK, TO-220 and TO-220FP packages





Features

Order code	V_{DS}	$R_{DS(on)}$ max.	I_D	P_{TOT}
STD7NK40ZT4	400 V	1 Ω	5.4 A	70 W
STP7NK40Z				70 W
STP7NK40ZFP				25 W

- Extremely high dv/dt capability
- 100% avalanche tested
- Gate charge minimized
- Very low intrinsic capacitance
- Zener-protected

Applications

- Switching applications

Description

These high-voltage devices are Zener-protected N-channel Power MOSFETs developed using the SuperMESH™ technology by STMicroelectronics, an optimization of the well-established PowerMESH™. In addition to a significant reduction in on-resistance, these devices are designed to ensure a high level of dv/dt capability for the most demanding applications.

Product status links
STD7NK40ZT4
STP7NK40Z
STP7NK40ZFP

Product summary	
STD7NK40ZT4	
Marking	D7NK40Z
Package	DPAK
Packing	Tape and reel
STP7NK40Z	
Marking	P7NK40Z
Package	TO-220
Packing	Tube
STP7NK40ZFP	
Marking	P7NK40ZFP
Package	TO-220FP
Packing	Tube

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value			Unit
		STD7NK40ZT4	STP7NK40Z	STP7NK40ZFP	
V_{DS}	Drain-source voltage	400			V
V_{DGR}	Drain-gate voltage (R_{GS} = 20 kΩ)	400			V
V_{GS}	Gate-source voltage	±30			V
I_D	Drain current (continuous) at T_C = 25 °C	5.4	5.4	5.4(1)	A
	Drain current (continuous) at T_C = 100 °C	3.4	3.4	3.4(1)	A
I_{DM}(2)	Drain current (pulsed)	21.6	21.6	21.6(1)	A
P_{TOT}	Total dissipation at T_C = 25 °C	70	70	25	W
I_{AR}	Avalanche current, repetitive or non-repetitive (pulse width is limited by T_J max.)	5.4			A
E_{AS}	Single pulse avalanche energy (starting T_J = 25 °C, I_D = I_{AR}, V_{DD} = 50 V)	130			mJ
ESD	Gate-source, human body model, R = 1.5 kΩ, C = 100 pF	3			kV
dv/dt(3)	Peak diode recovery voltage slope	4.5			V/ns
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s, T_C = 25 °C)			2.5	kV
T_J	Operating junction temperature range	-55 to 150			°C
T_{stg}	Storage temperature range				

1. *This value is limited by maximum junction temperature.*
2. *Pulse width is limited by safe operating area.*
3. *I_{SD} ≤ 5.4 A, di/dt ≤ 200 A/µs, V_{DD} < $V_{(BR)DSS}$*

Table 2. Thermal data

Symbol	Parameter	Value			Unit
		DPAK	TO-220	TO-220FP	
$R_{thj\text{-}case}$	Thermal resistance junction-case	1.78	1.78	5	°C/W
$R_{thj\text{-}amb}$	Thermal resistance junction-ambient		62.5		°C/W
$R_{thj\text{-}pcb}$(1)	Thermal resistance junction-pcb	50			°C/W

1. *When mounted on an 1-inch² FR-4, 2 Oz copper board.*

2 Electrical characteristics

(T_C = 25 °C unless otherwise specified)

Table 3. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	I_D = 1 mA, V_{GS} = 0 V	400			V
I_{DSS}	Zero gate voltage drain current	V_{GS} = 0 V, V_{DS} = 400 V			1	µA
		V_{GS} = 0 V, V_{DS} = 400 V, T_C = 125 °C(1)			50	µA
I_{GSS}	Gate body leakage current	V_{GS} = ±20 V, V_{DS} = 0 V			±10	µA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 50 µA	3	3.75	4.5	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D = 2.7 A		0.85	1	Ω

1. *Defined by design, not subject to production test.*

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS} = 25 V, f = 1 MHz, V_{GS} = 0 V	-	535	-	pF
C_{oss}	Output capacitance			82		
C_{rss}	Reverse transfer capacitance			18		
$C_{oss\ eq.}$(1)	Equivalent output capacitance	V_{GS} = 0 V, V_{DS} = 0 to 320 V	-	53	-	pF
Q_g	Total gate charge	V_{DD} = 320 V, I_D = 5.4 A, V_{GS} = 0 to 10 V (see Figure 16. Test circuit for gate charge behavior)	-	19	26	nC
Q_{gs}	Gate-source charge			4		
Q_{gd}	Gate-drain charge			10		

1. *$C_{oss\ eq.}$ is defined as the constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}.*

Table 5. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD} = 200 V, I_D = 2.7 A, R_G = 4.7 Ω, V_{GS} = 10 V (see Figure 15. Test circuit for resistive load switching times and Figure 20. Switching time waveform)	-	15	-	ns
t_r	Rise time			15		
$t_{d(off)}$	Turn-off delay time			30		
t_f	Fall time			12		
$t_{r(Voff)}$	Off-voltage rise time	V_{DD} = 320 V, I_D = 5.4 A, R_G = 4.7 Ω, V_{GS} = 10 V (see Figure 17. Test circuit for inductive load switching and diode recovery times)	-	12	-	
t_f	Fall time			10		
t_c	Crossover time			20		

Table 6. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		5.4	A
I_{SDM}(1)	Source-drain current (pulsed)				21.6	
V_{SD}(2)	Forward on voltage	I_{SD} = 5.4 A, V_{GS} = 0 V	-		1.6	V
t_{rr}	Reverse recovery time	I_{SD} = 5.4 A, di/dt = 100 A/µs, V_{DD} = 50 V, T_J = 150 °C (see Figure 17. Test circuit for inductive load switching and diode recovery times)	-	220		ns
Q_{rr}	Reverse recovery charge			990		nC
I_{RRM}	Reverse recovery current			9		A

1. *Pulsed: pulse duration = 300 µs, duty cycle 1.5%.*
2. *Pulse width is limited by safe operating area.*

Table 7. Gate-source Zener diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)GSO}$	Gate-source breakdown voltage	I_{GS} = ±1 mA (open drain)	30	-	-	V

The built-in back-to-back Zener diodes are specifically designed to enhance the ESD performance of the device. The Zener voltage facilitates efficient and cost-effective device integrity protection, thus eliminating the need for additional external componentry.

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area for TO-220/DPAK

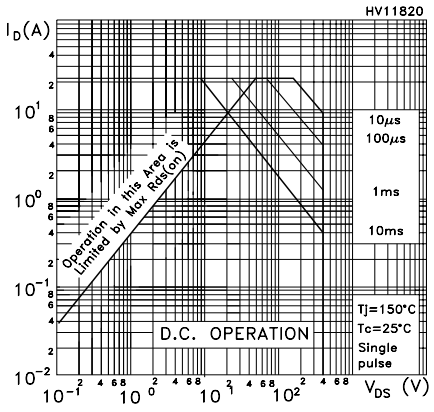


Figure 2. Thermal impedance for TO-220/DPAK

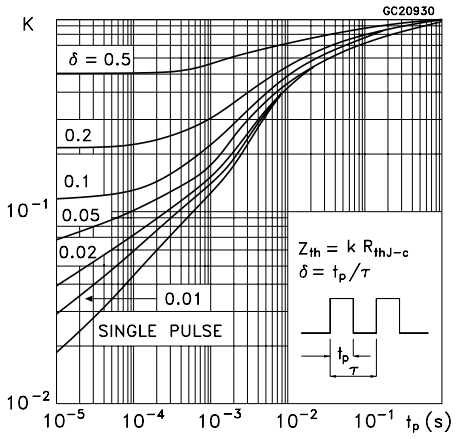


Figure 3. Safe operating area for TO-220FP

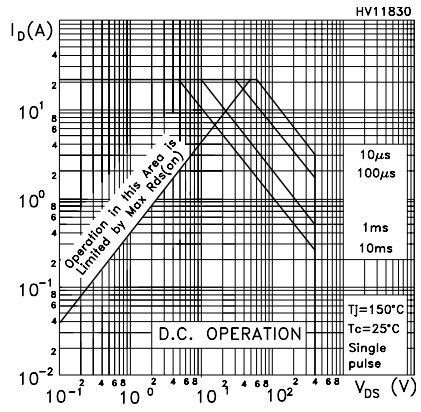


Figure 4. Thermal impedance for TO-220FP

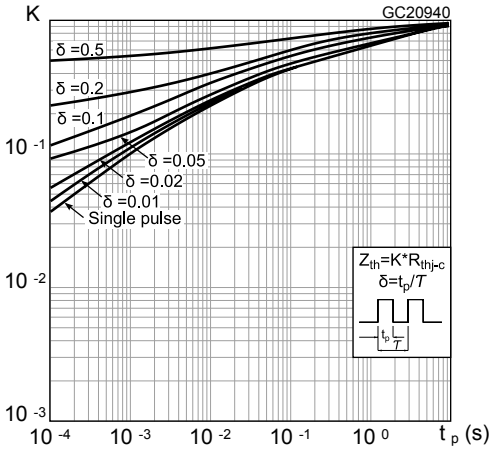


Figure 5. Output characteristics

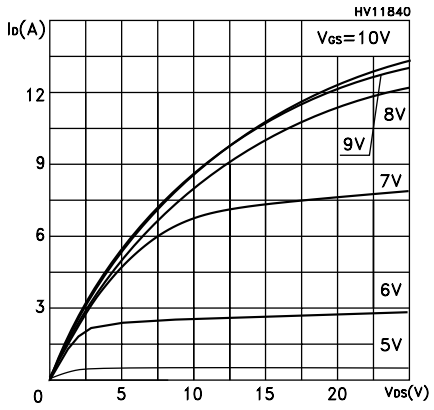


Figure 6. Transfer characteristics

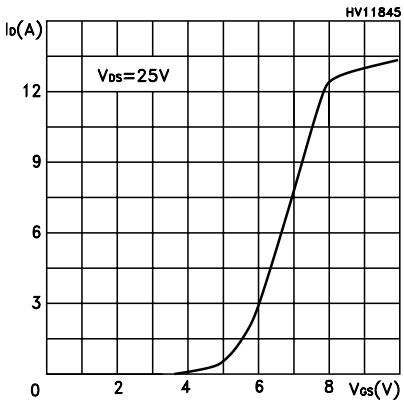


Figure 7. Static drain-source on-resistance

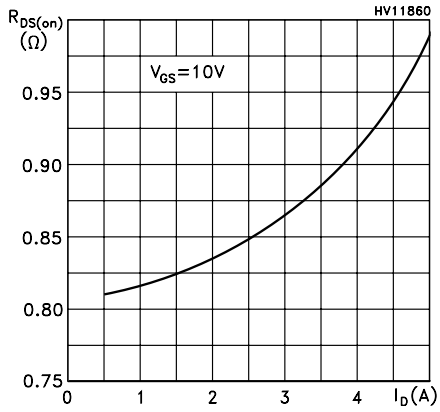


Figure 8. Gate charge vs gate-source voltage

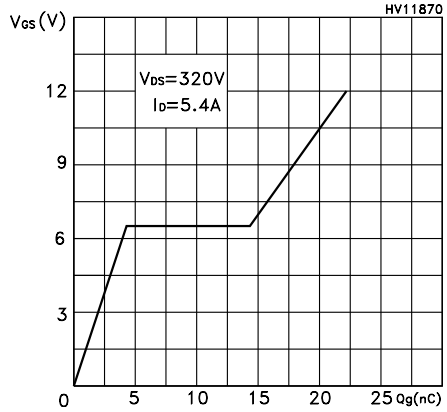


Figure 9. Capacitance variations

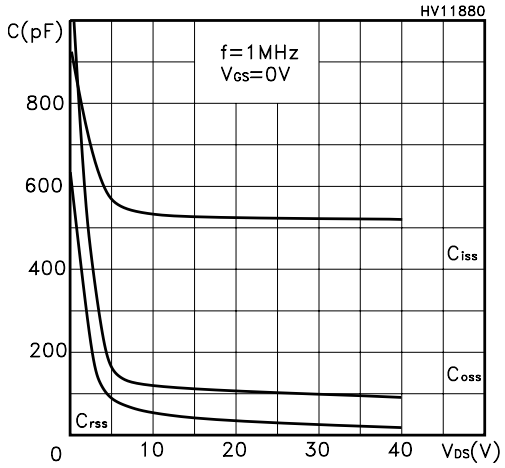


Figure 10. Normalized gate threshold voltage vs temperature

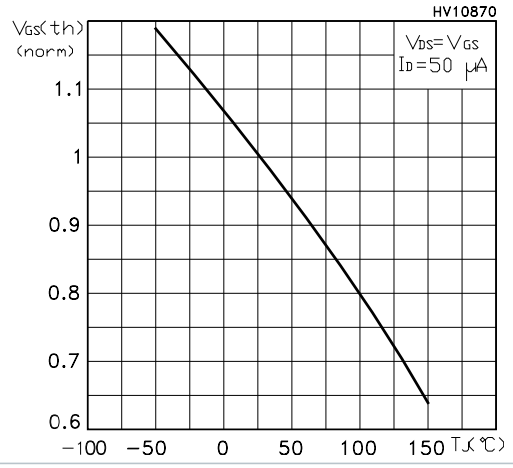


Figure 11. Normalized on-resistance vs temperature

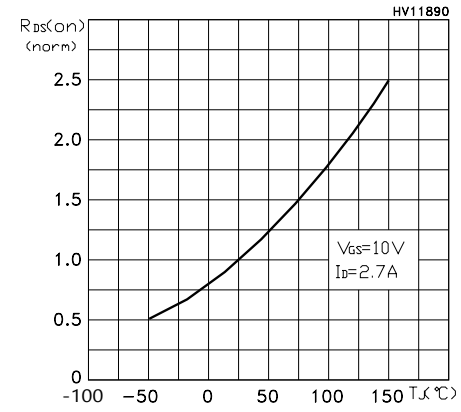


Figure 12. Source-drain diode forward characteristics

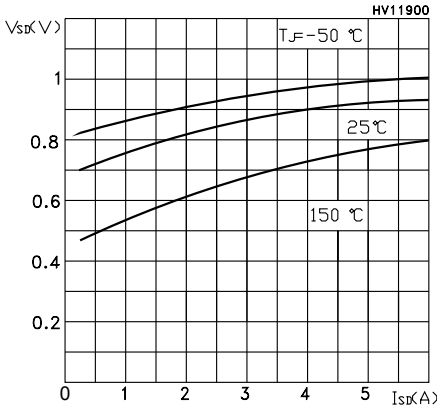


Figure 13. Normalized $V_{(BR)DSS}$ vs temperature

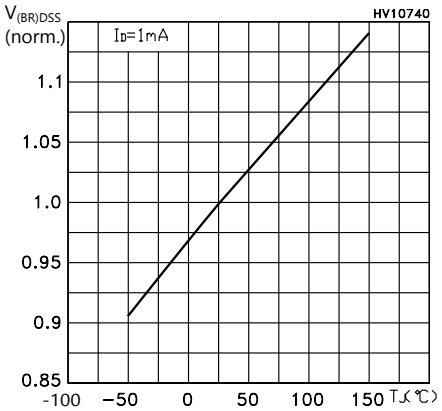
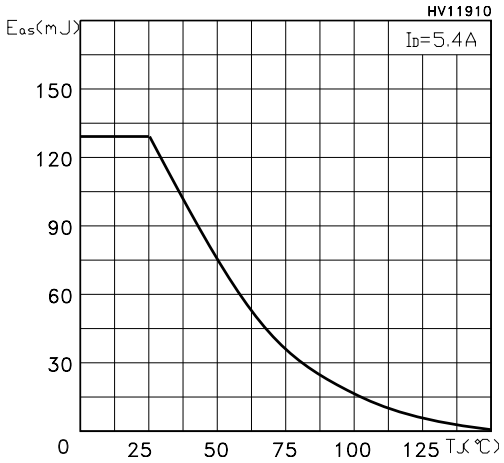


Figure 14. Maximum avalanche energy vs temperature



3 Test circuits

Figure 15. Test circuit for resistive load switching times

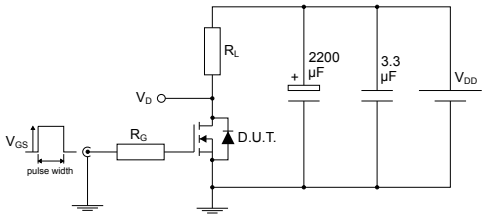


Figure 16. Test circuit for gate charge behavior

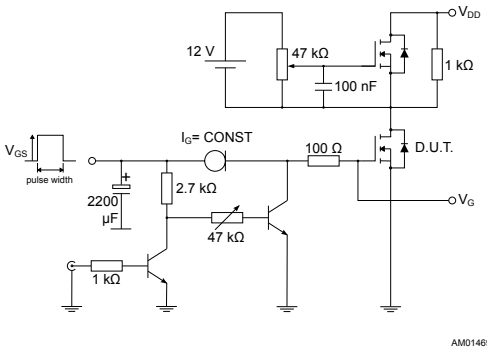


Figure 17. Test circuit for inductive load switching and diode recovery times

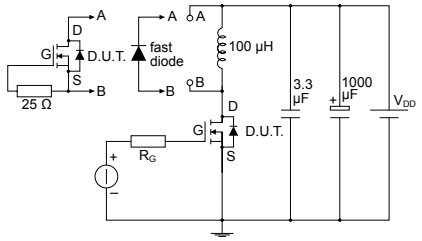


Figure 18. Unclamped inductive load test circuit

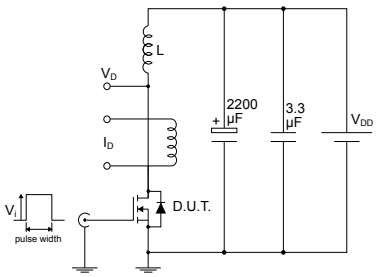


Figure 19. Unclamped inductive waveform

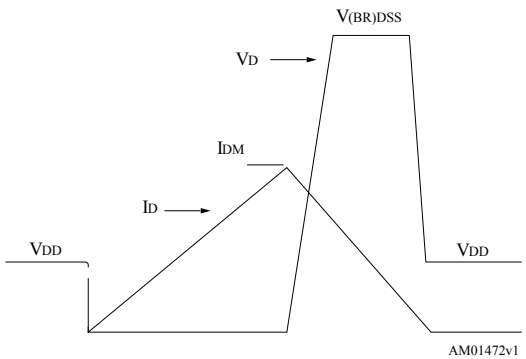
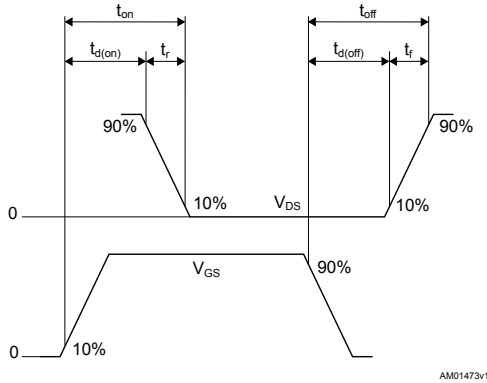


Figure 20. Switching time waveform



4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

4.1 DPAK (TO-252) type A package information

Figure 21. **DPAK (TO-252) type A package outline**

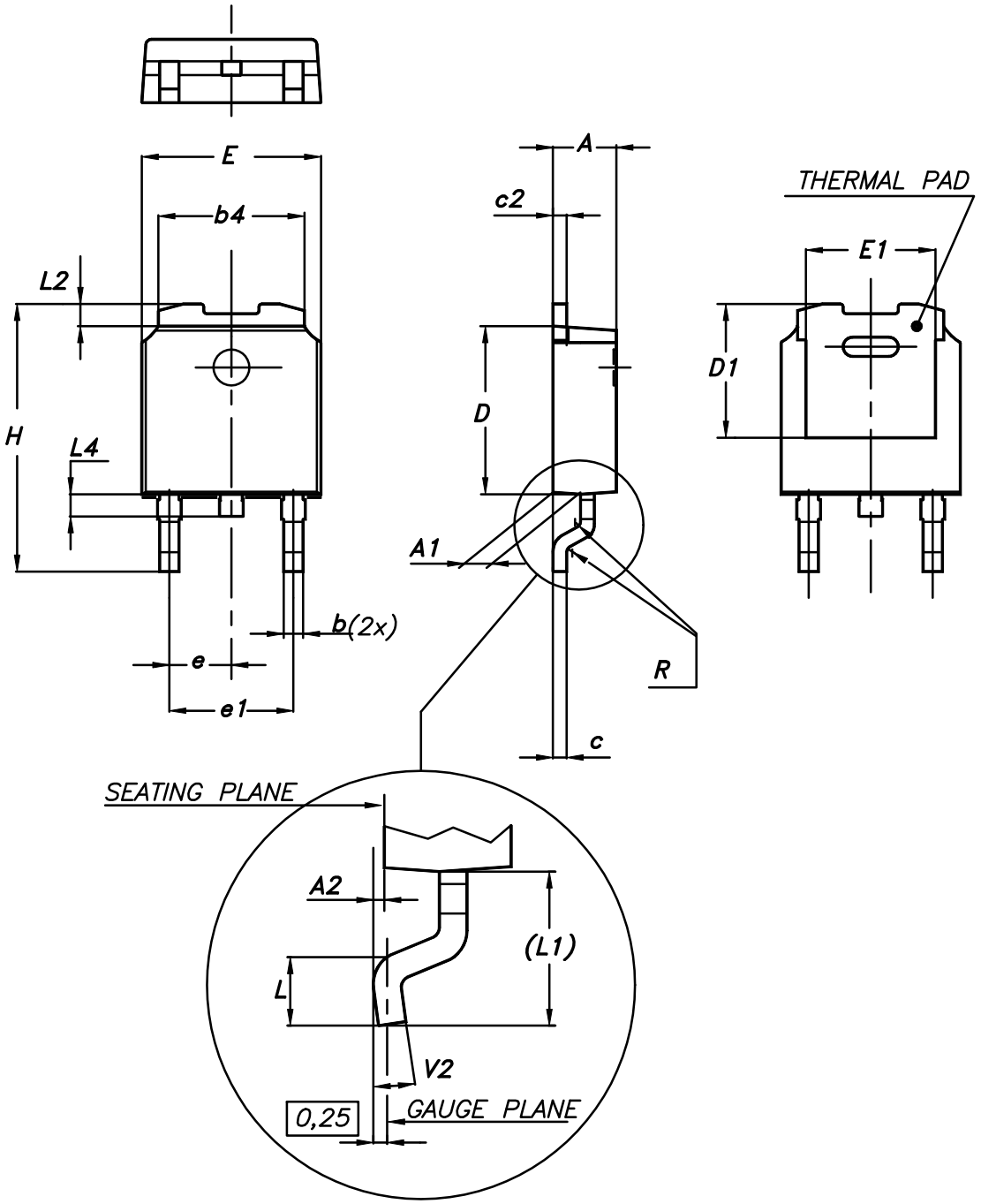


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Table 8. **DPAK (TO-252) type A mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1	4.95	5.10	5.25
E	6.40		6.60
E1	4.60	4.70	4.80
e	2.159	2.286	2.413
e1	4.445	4.572	4.699
H	9.35		10.10
L	1.00		1.50
(L1)	2.60	2.80	3.00
L2	0.65	0.80	0.95
L4	0.60		1.00
R		0.20	
V2	0°		8°

4.2 DPAK (TO-252) type E package information

Figure 22. **DPAK (TO-252) type E package outline**

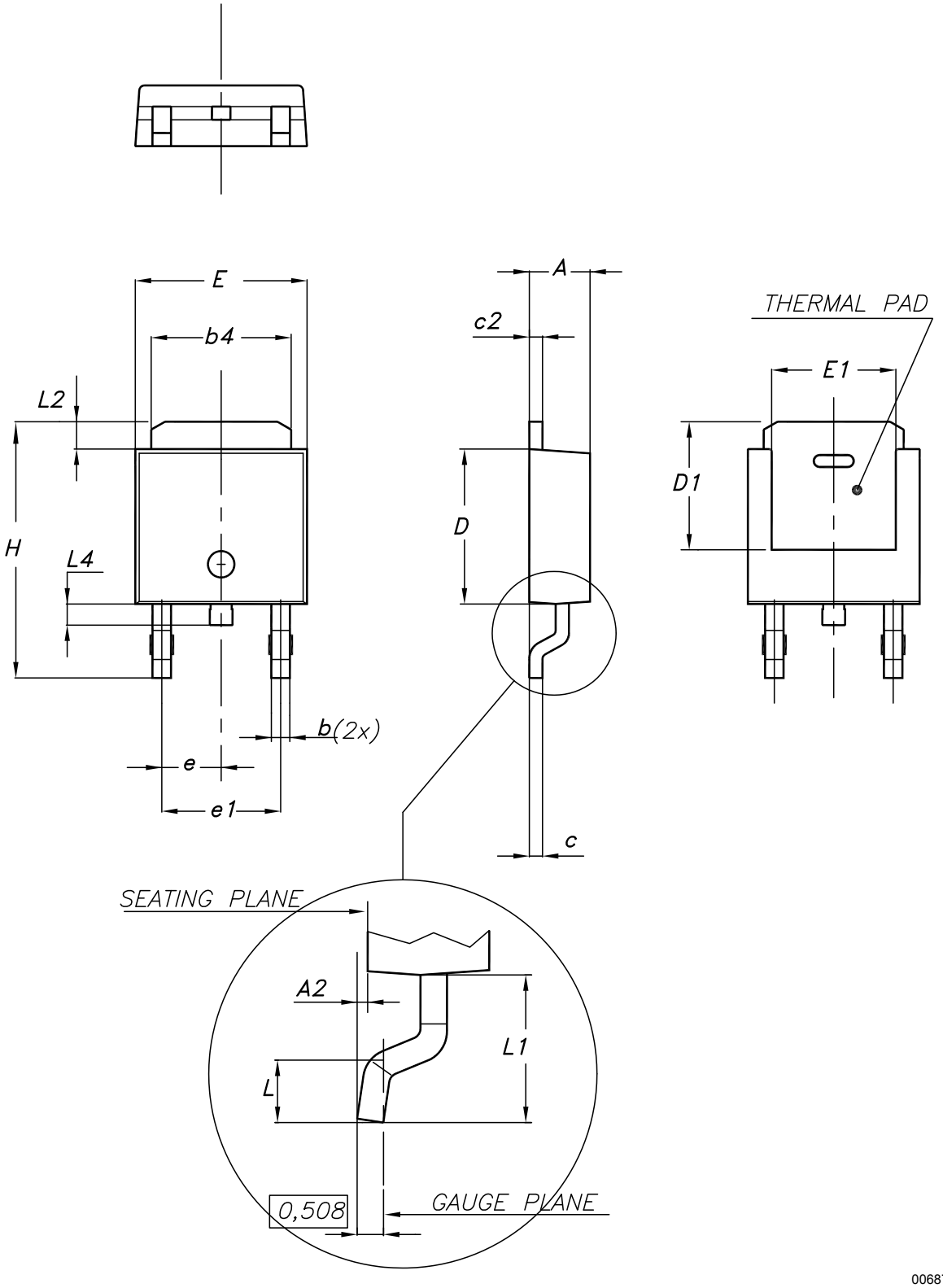

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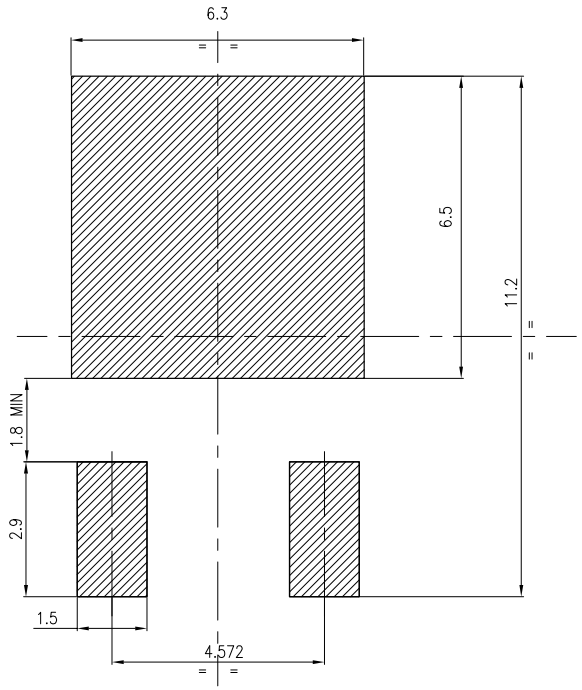
Table 9. DPAK (TO-252) type E mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.18		2.39
A2			0.13
b	0.65		0.884
b4	4.95		5.46
c	0.46		0.61
c2	0.46		0.60
D	5.97		6.22
D1	5.21		
E	6.35		6.73
E1	4.32		
e		2.286	
e1		4.572	
H	9.94		10.34
L	1.50		1.78
L1		2.74	
L2	0.89		1.27
L4			1.02

Figure 23. DPAK (TO-252) recommended footprint (dimensions are in mm)



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4.3 DPAK (TO-252) packing information

Figure 24. **DPAK (TO-252) tape outline**

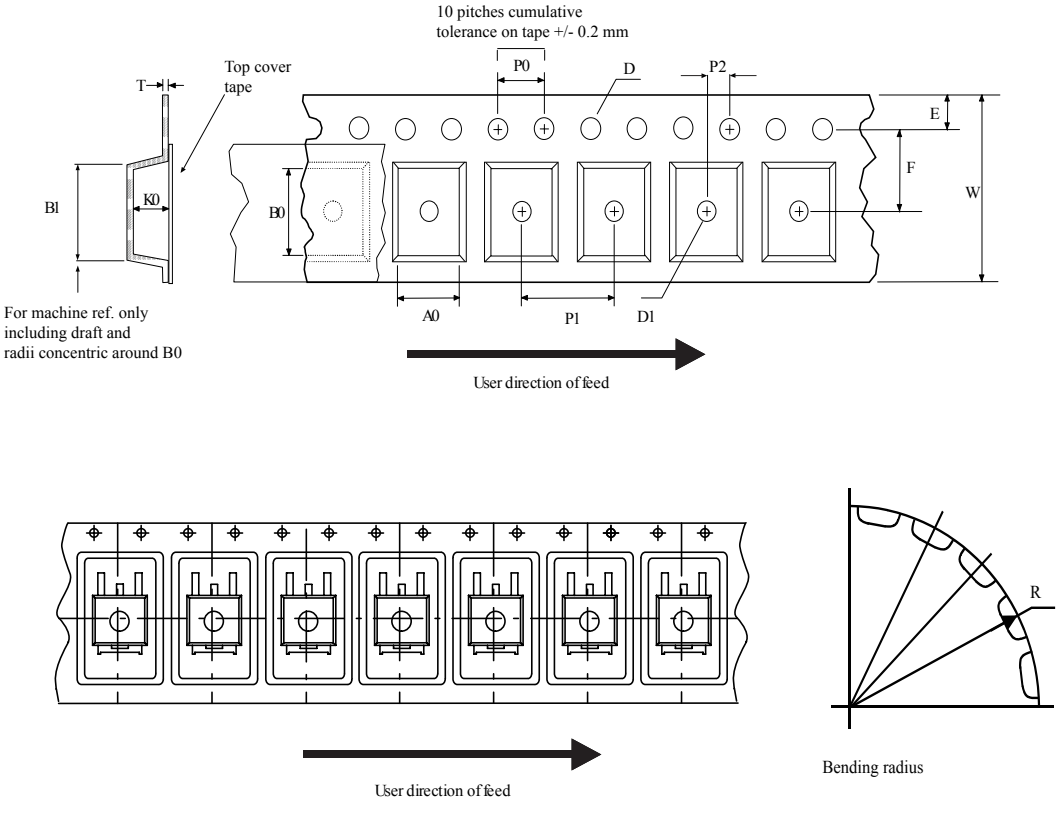

Figure 25. **DPAK (TO-252) reel outline**

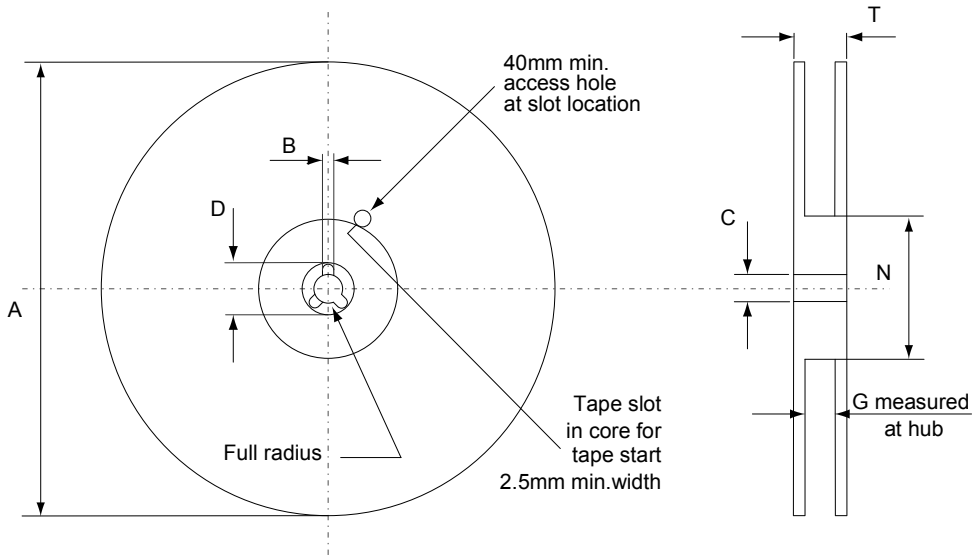

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Table 10. **DPAK (TO-252) tape and reel mechanical data**

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

4.4 TO-220 type A package information

Figure 26. **TO-220 type A package outline**

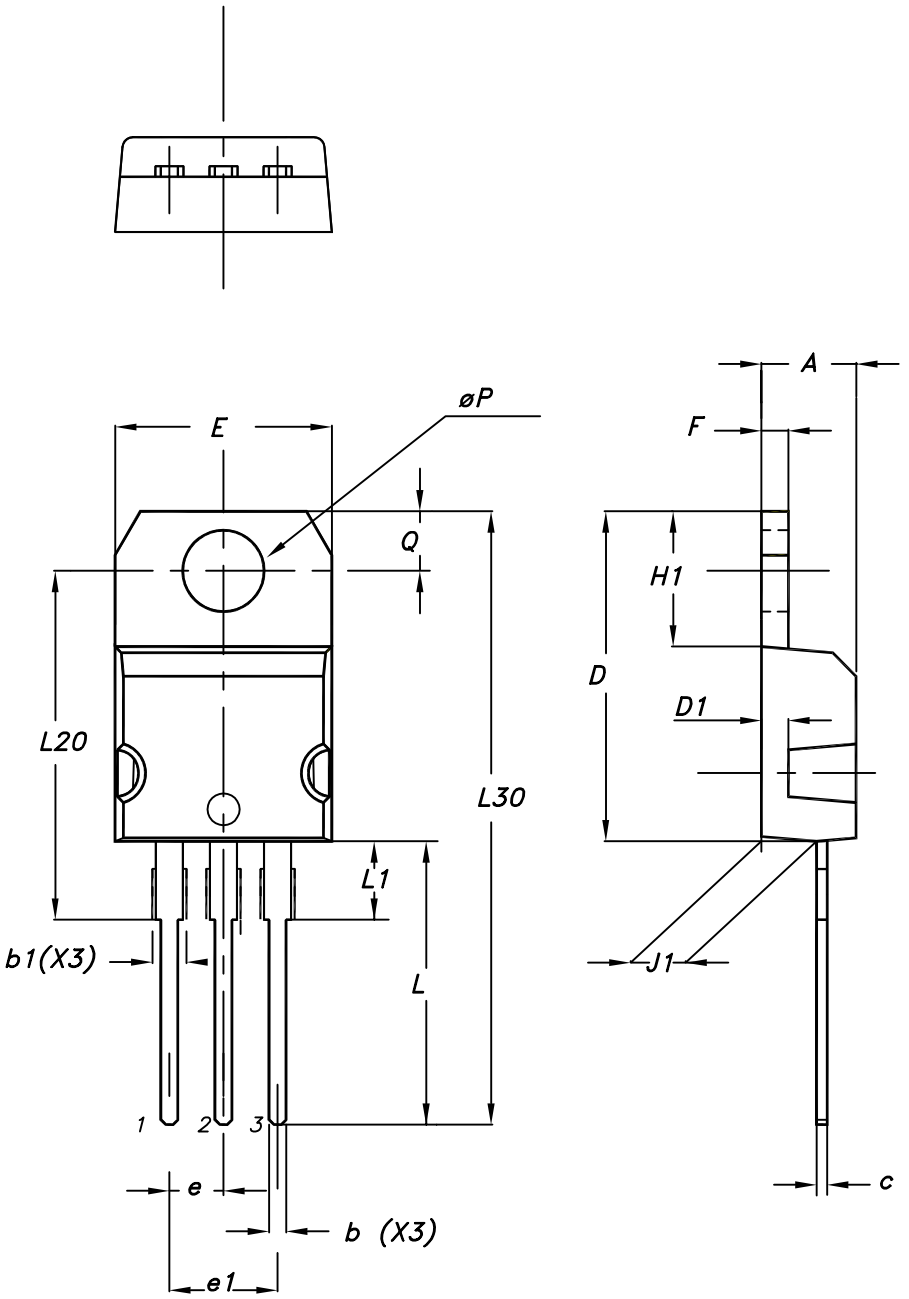

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Table 11. **TO-220 type A package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.55
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10.00		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13.00		14.00
L1	3.50		3.93
L20		16.40	
L30		28.90	
øP	3.75		3.85
Q	2.65		2.95

4.5 TO-220FP package information

Figure 27. **TO-220FP package outline**

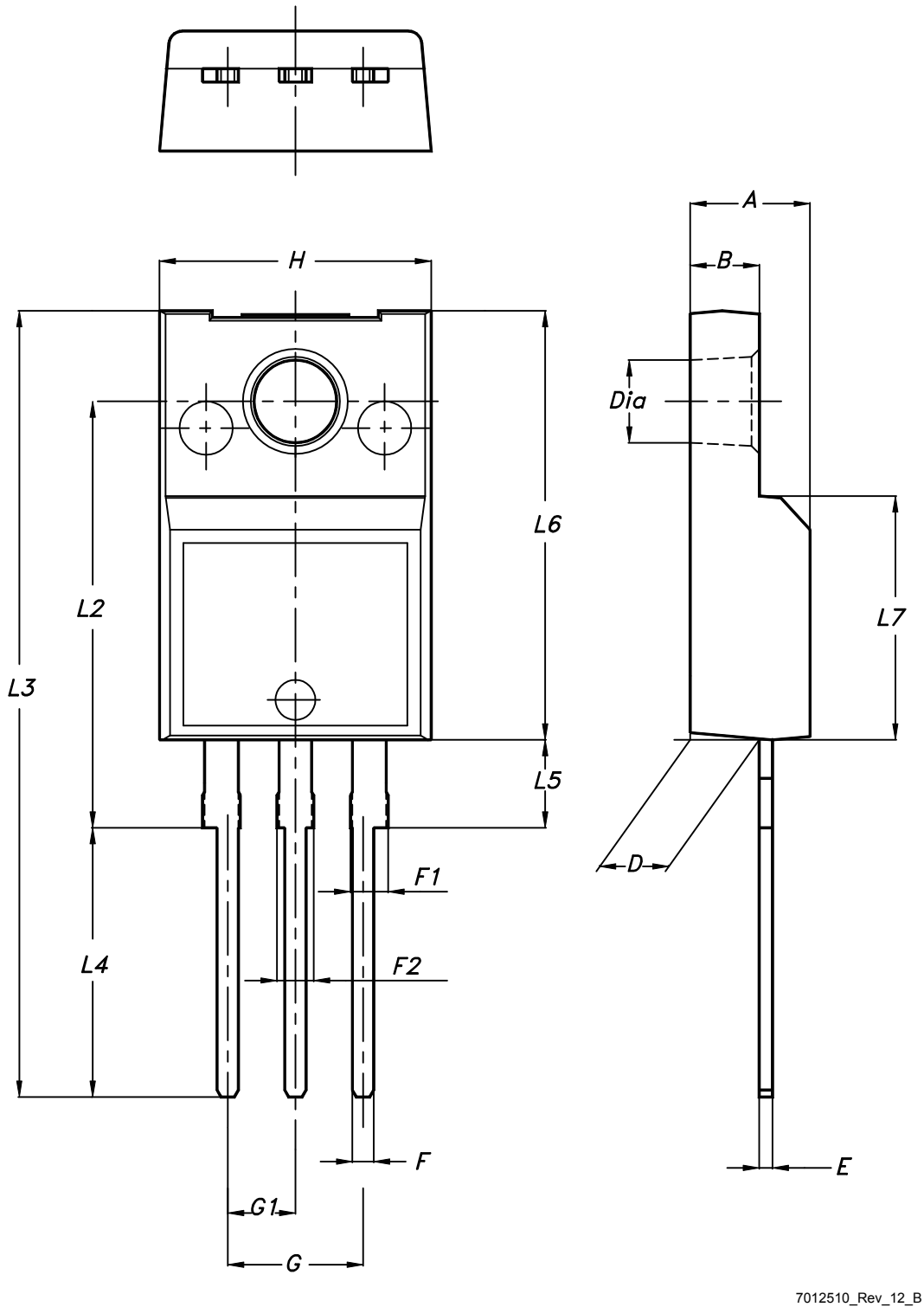

Table 12. **TO-220FP package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

Revision history

Table 13. **Document revision history**

Date	Version	Changes
02-Sep-2002	2	Document updated.
11-Jul-2018	3	Part number STD7NK40Z-1 was moved to a separate datasheet, and the document was updated accordingly. Updated title, features, applications and description on cover page. Updated Section 1 Electrical ratings, Section 2 Electrical characteristics, Section 3 Test circuits and Section 4 Package information. Minor text changes

Contents

Общество с ограниченной ответственностью «МосЧип» ИНН 7719860671 / КПП 771901001
Адрес: 105318, г.Москва, ул.Щербаковская д.3, офис 1107

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Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

http://moschip.ru/get-element

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:
moschip.ru
moschip.ru_4
moschip.ru_6
moschip.ru_9